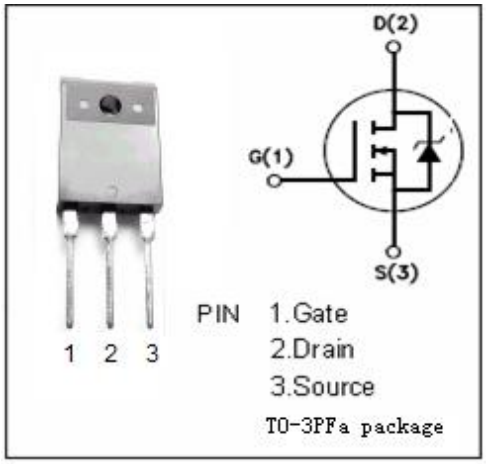
isc N-Channel MOSFET Transistor 2SK635

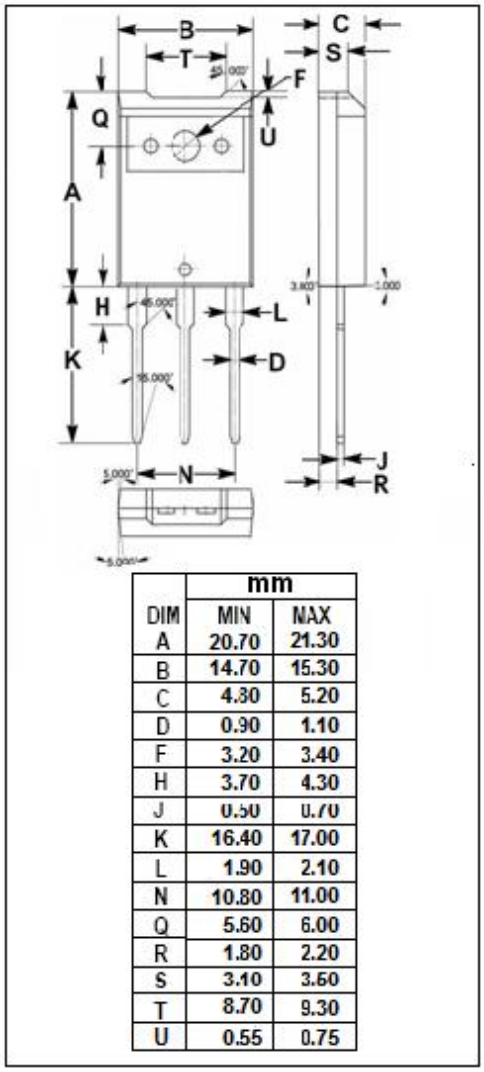


FEATURES

- Drain Current $-I_D$=3A@ T_C=25℃
- Drain Source Voltage-
  : V_{DSS}= 500V(Min)

DESCRIPTION

- Designed for high voltage, high speed power switching applications such as switching regulators, converters, solenoid and relay drivers.



DIM	mm MIN	MAX
A	20.70	21.30
B	14.70	15.30
C	4.30	5.20
D	0.90	1.10
F	3.20	3.40
H	3.70	4.30
J	0.50	0.70
K	16.40	17.00
L	1.90	2.10
N	10.80	11.00
Q	5.60	6.00
R	1.80	2.20
S	3.10	3.60
T	8.70	9.30
U	0.55	0.75

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	500	V
V_{GS}	Gate-Source Voltage-Continuous	±20	V
I_D	Drain Current-Continuous	3	A
P_D	Total Dissipation @T_C=25℃	40	W
T_J	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	1.25	℃/W
$R_{th\ j\text{-}a}$	Thermal Resistance, Junction to Ambient	62.5	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D= 1mA	500			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}; I_D= 1mA	1.0		5.0	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 15V; I_D= 2A			4.5	Ω
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±20V;V_{DS}= 0			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=500V; V_{GS}=0			1	μA

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